



### Product Summary

- $V_{DS} = -20V, I_D = -4.1A$
- $R_{DS(ON)} < 75m\Omega @ V_{GS}=-2.5V$
- $R_{DS(ON)} < 52m\Omega @ V_{GS}=-4.5V$
- Advanced Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired

### Application

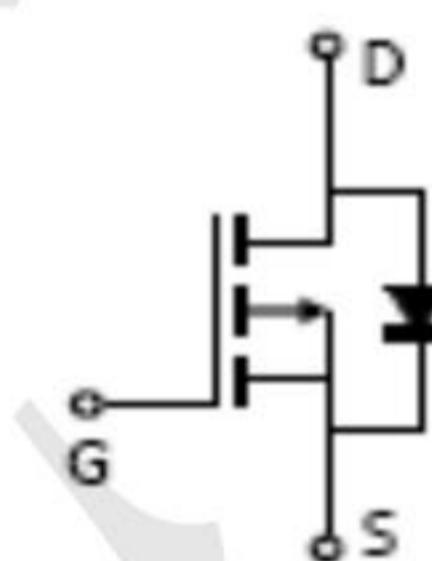
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

### Package and Pin Configuration

SOT-23



Circuit diagram



### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	-4.1	A
		-3.2	
		-3	
		-2.3	
Drain Current -Pulsed (Note 1)	$I_{DM}$	-15	A
Maximum Power Dissipation	$P_D$	1.7	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	74	°C/W
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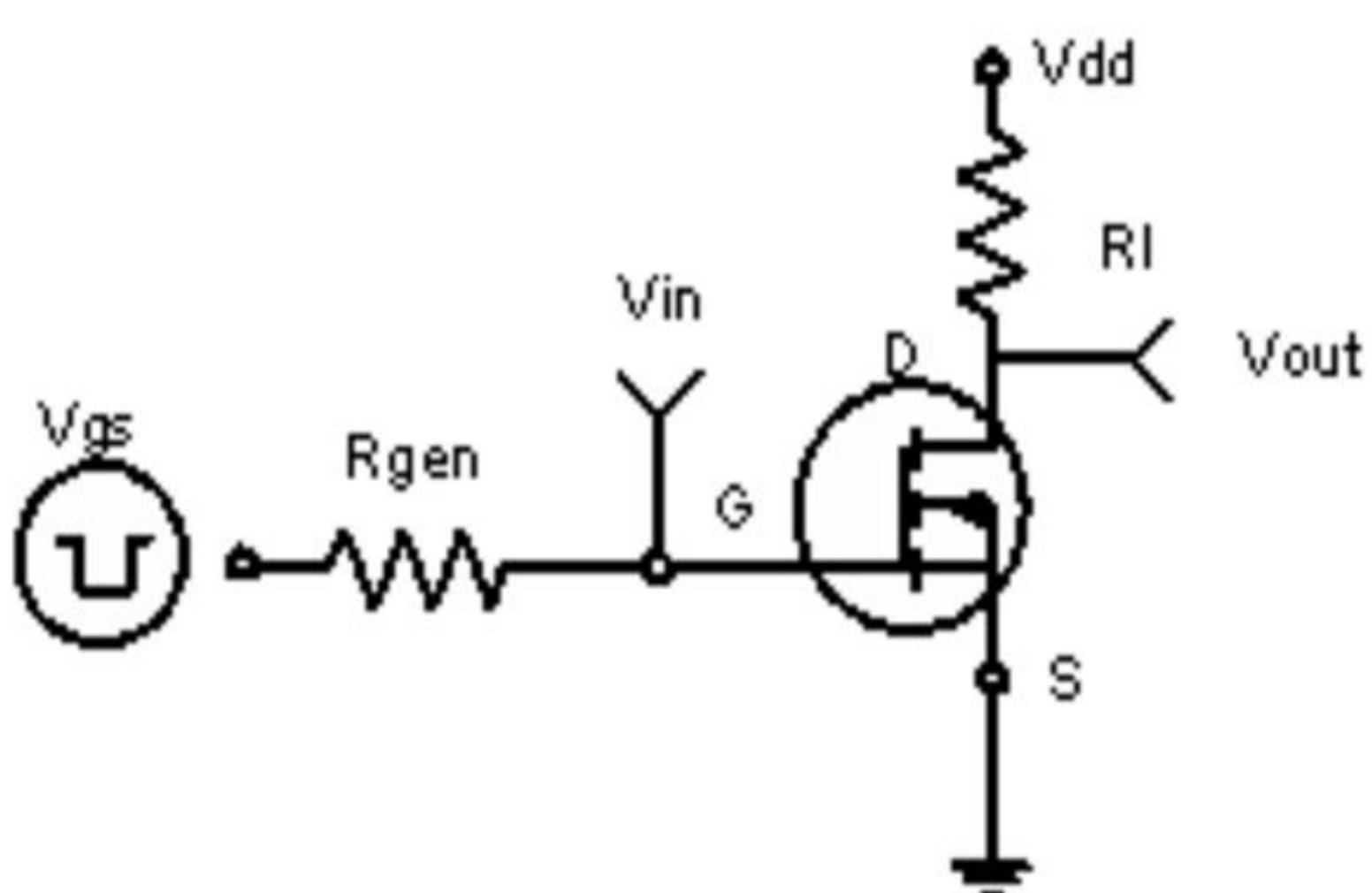


**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

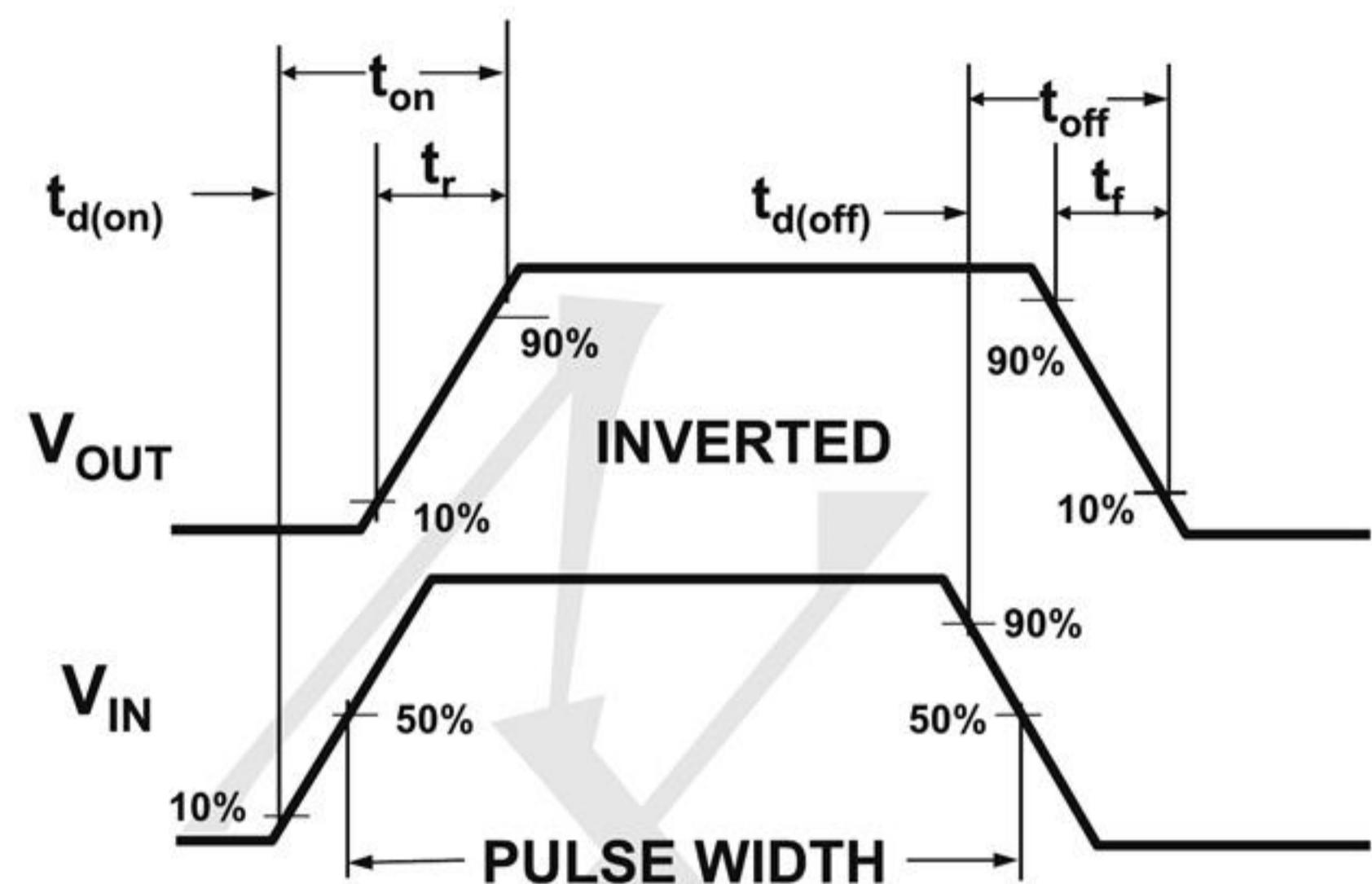
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.45	-0.7	-1.0	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4.1\text{A}$	-	39	52	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-3\text{A}$	-	58	75	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-2\text{A}$	6	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-4\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	740	-	PF
Output Capacitance	$C_{\text{oss}}$		-	290	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	190	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-4\text{V}, I_{\text{D}}=-3.3\text{A}, R_{\text{L}}=-1.2\Omega, V_{\text{GEN}}=-4.5\text{V}, R_{\text{g}}=1\Omega$	-	12	-	nS
Turn-on Rise Time	$t_{\text{r}}$		-	35	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	30	-	nS
Turn-Off Fall Time	$t_{\text{f}}$		-	10	-	nS
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=-4\text{V}, I_{\text{D}}=-4.1\text{A}, V_{\text{GS}}=-4.5\text{V}$	-	7.8	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	1.2	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	1.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1.6\text{A}$	-	-	-1.2	V
Diode Forward Current (Note 2)	$I_{\text{S}}$		-	-	1.6	A



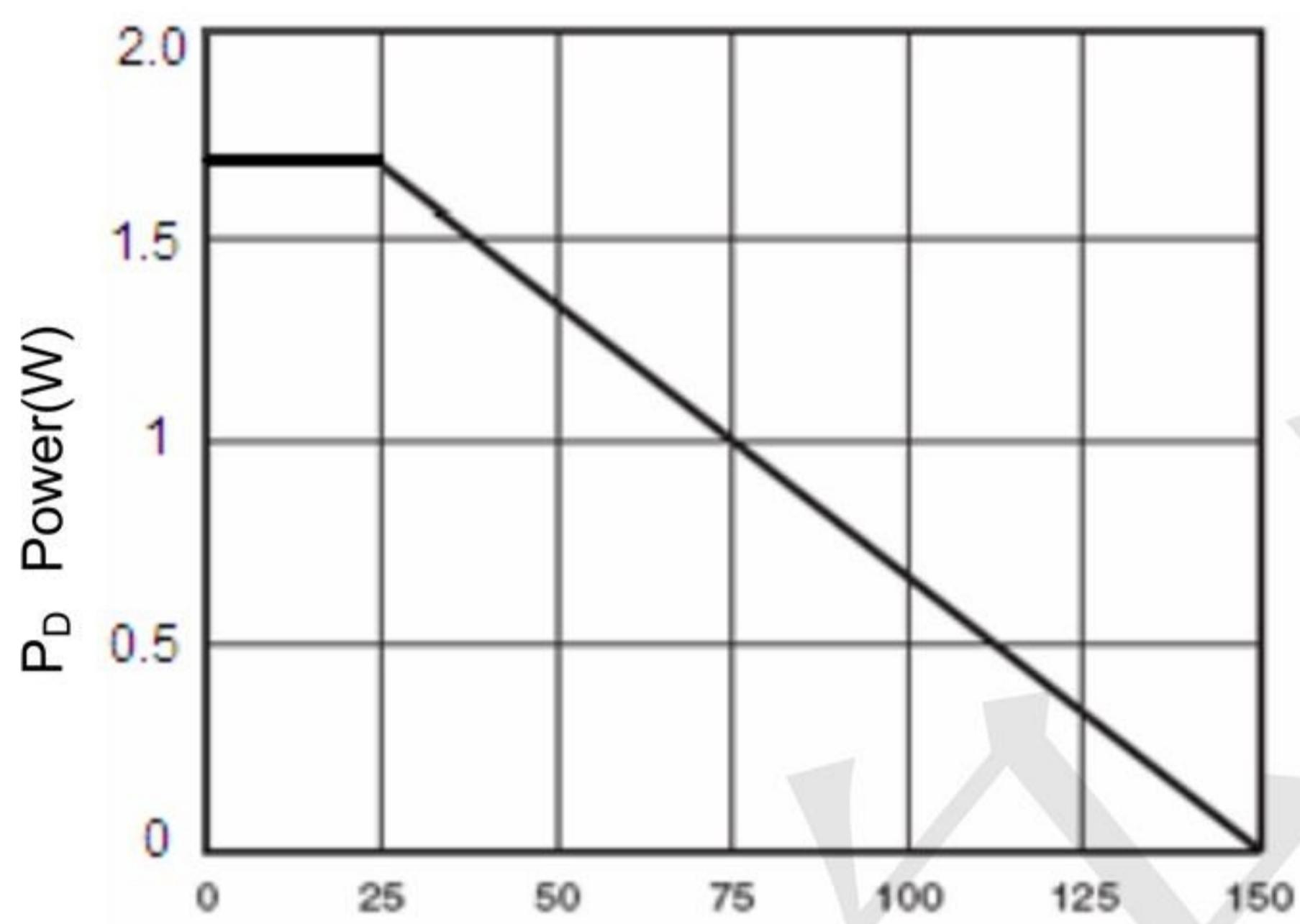
### Typical Electrical and Thermal Characteristics



**Figure 1:Switching Test Circuit**

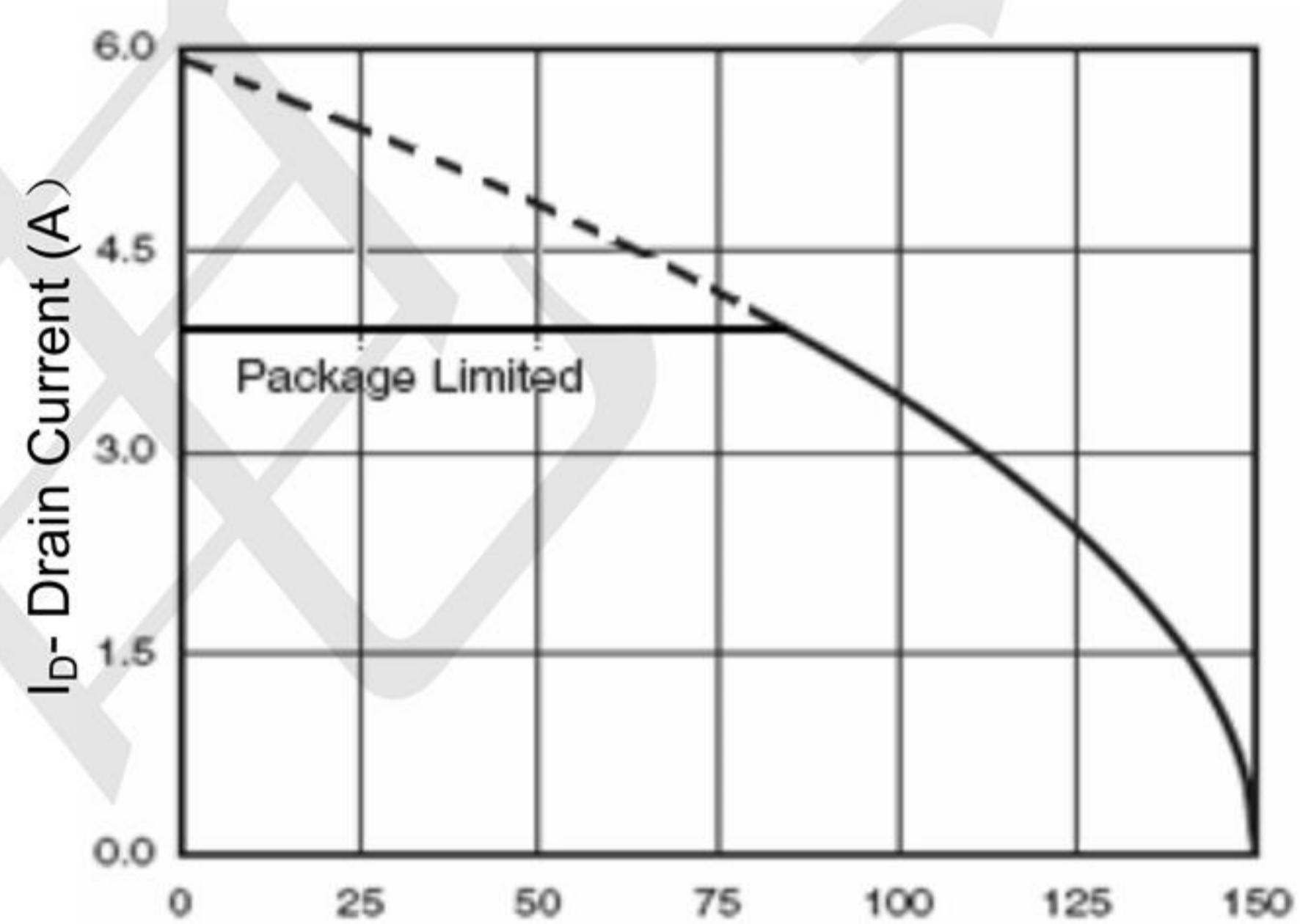


**Figure 2:Switching Waveforms**



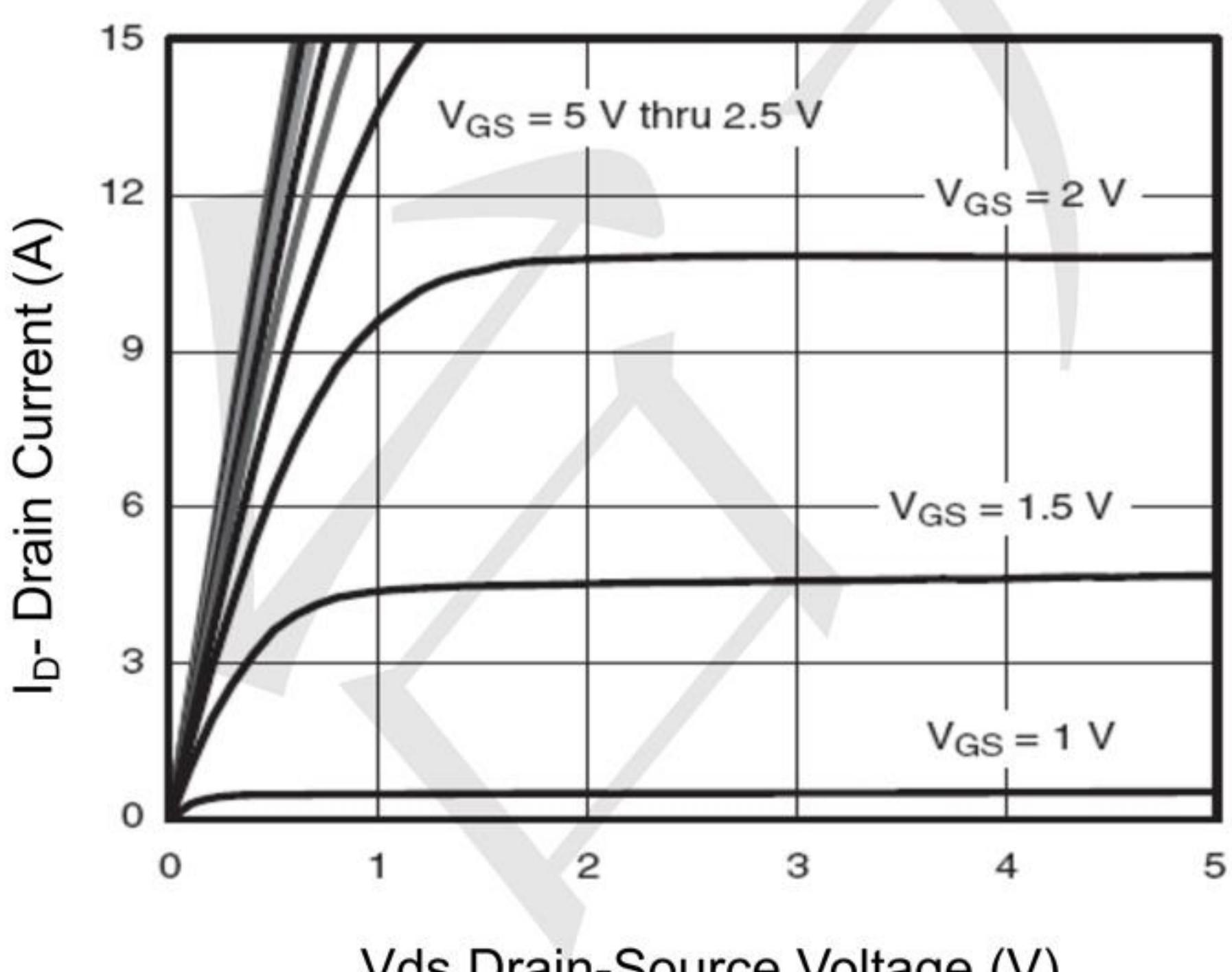
T<sub>J</sub>-Junction Temperature(°C)

**Figure 3 Power Dissipation**

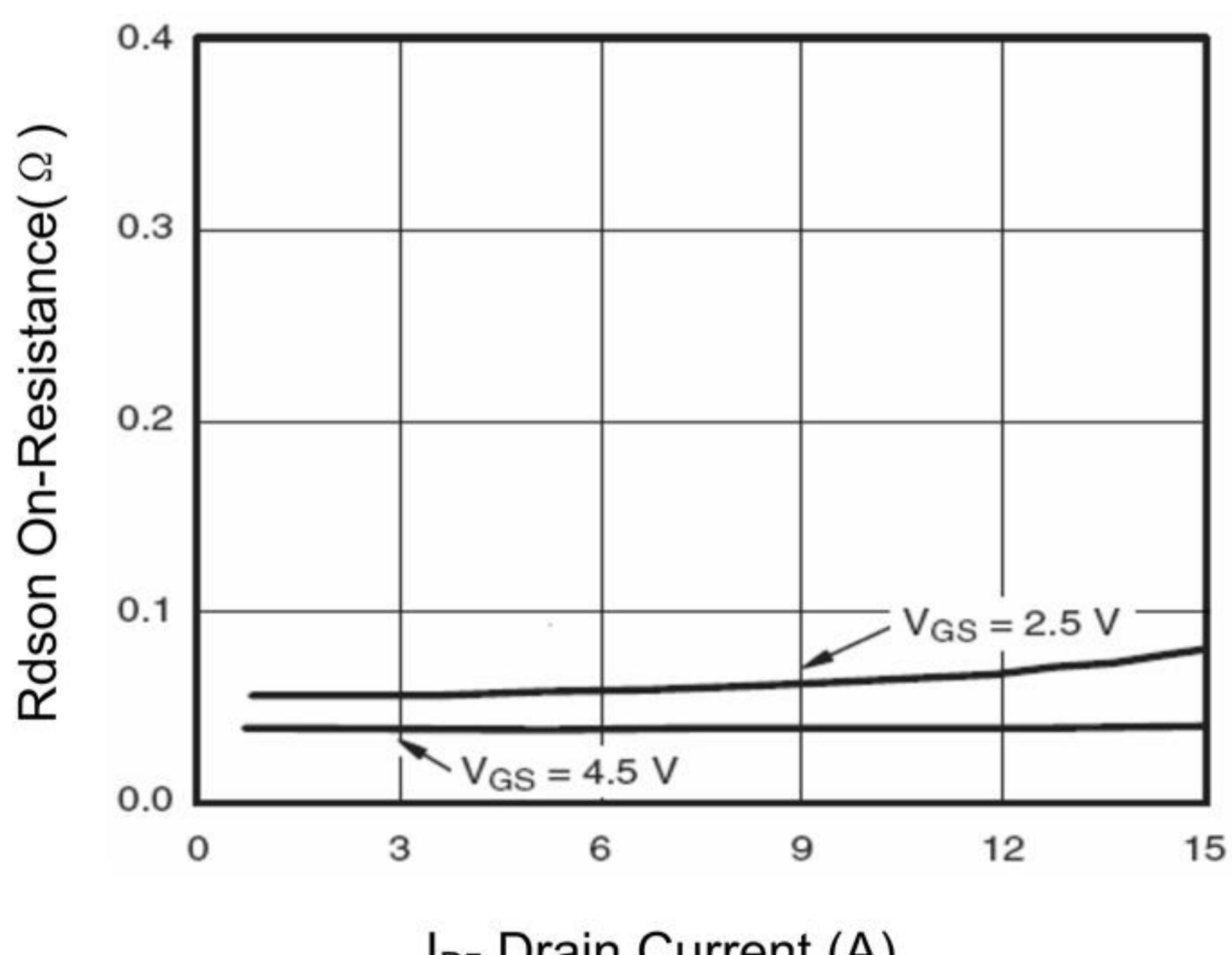


T<sub>J</sub>-Junction Temperature(°C)

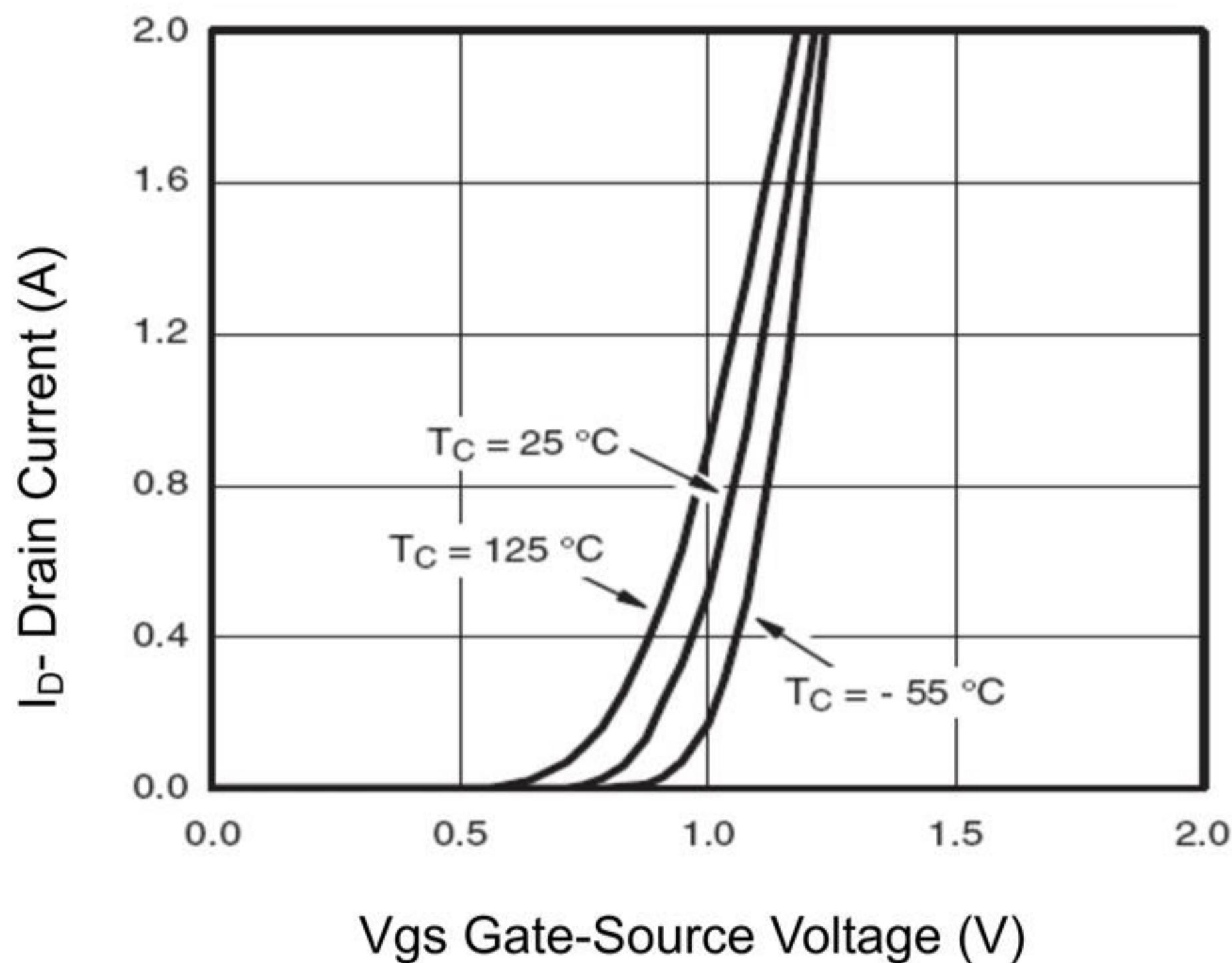
**Figure 4 Drain Current**



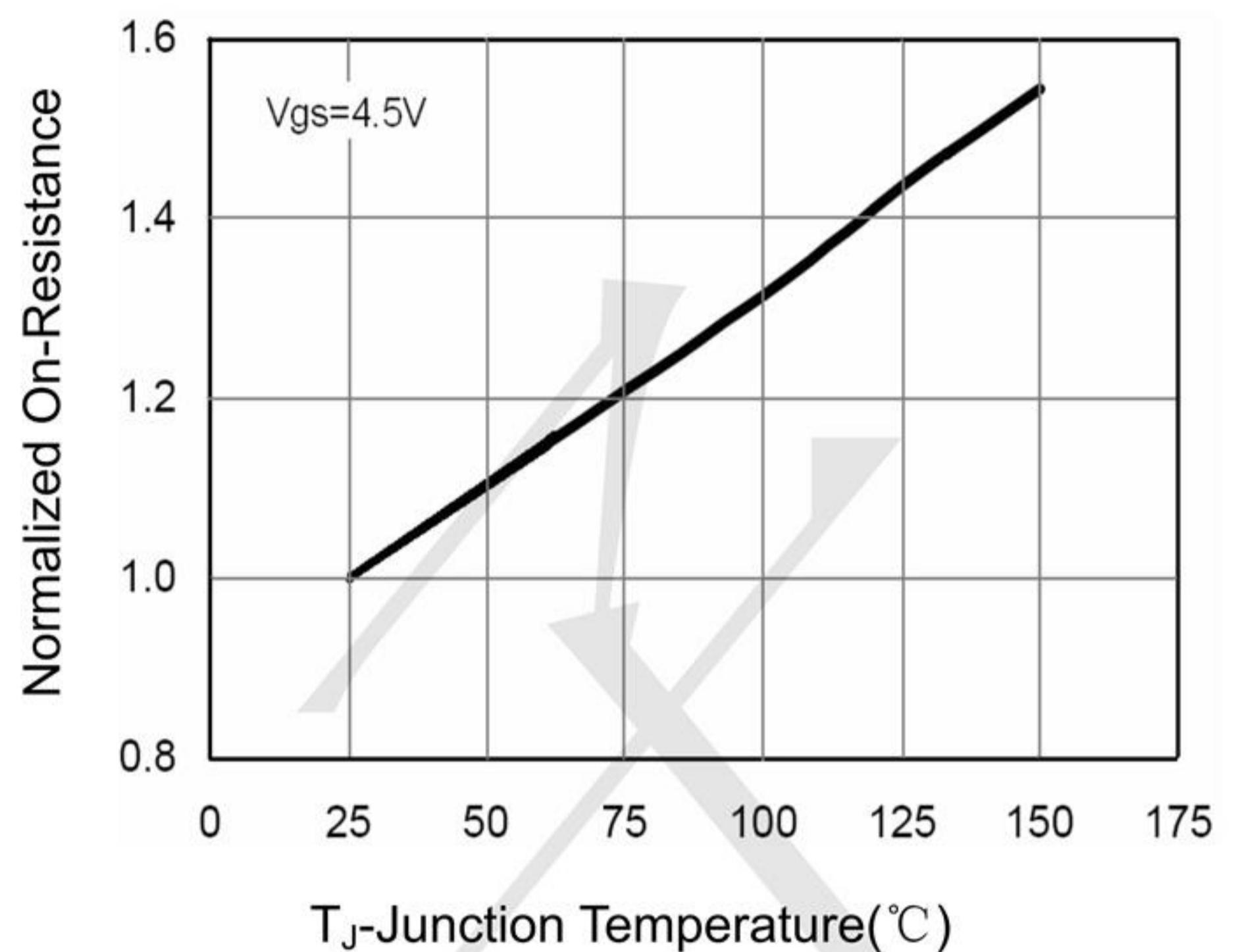
**Figure 5 Output Characteristics**



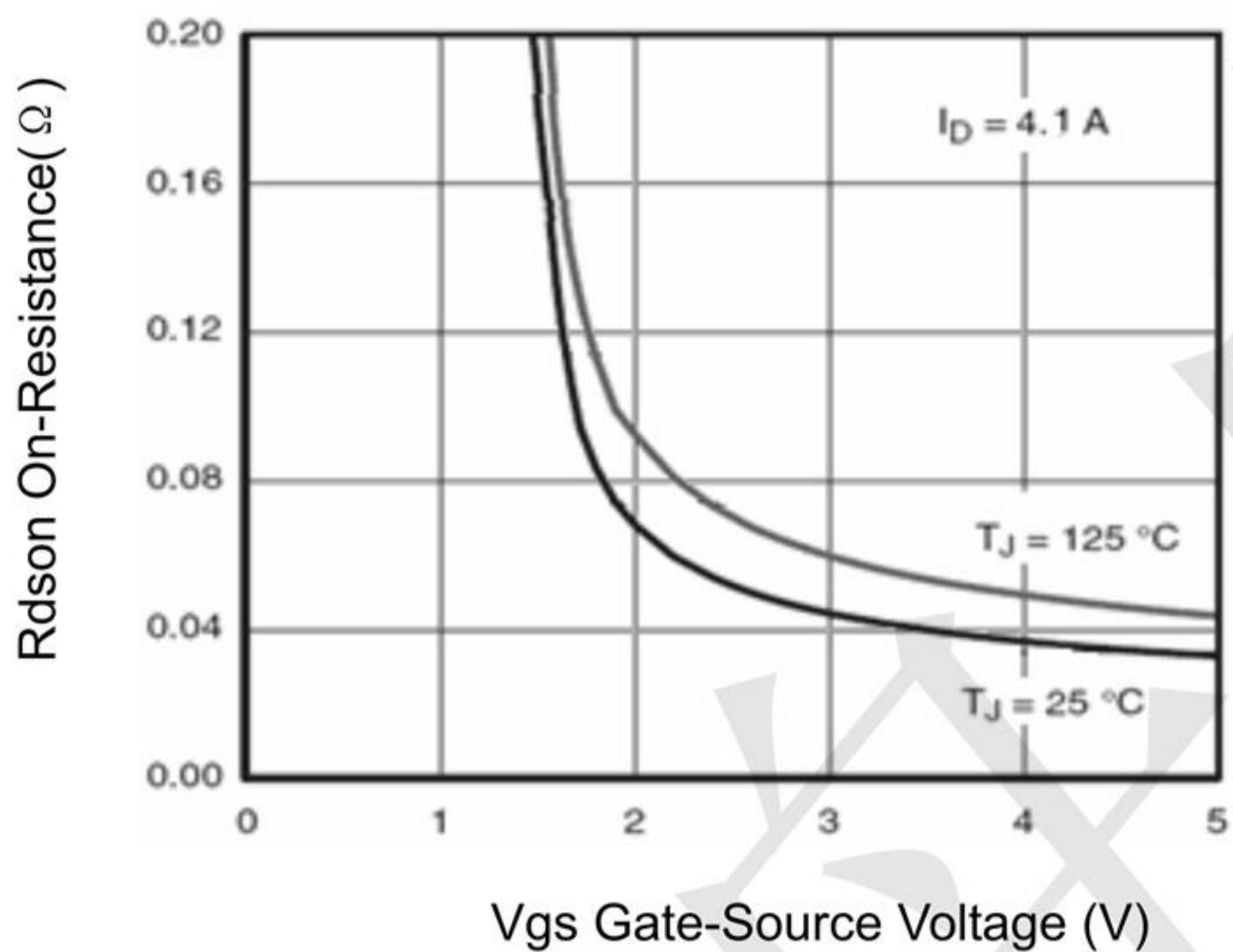
**Figure 6 Drain-Source On-Resistance**



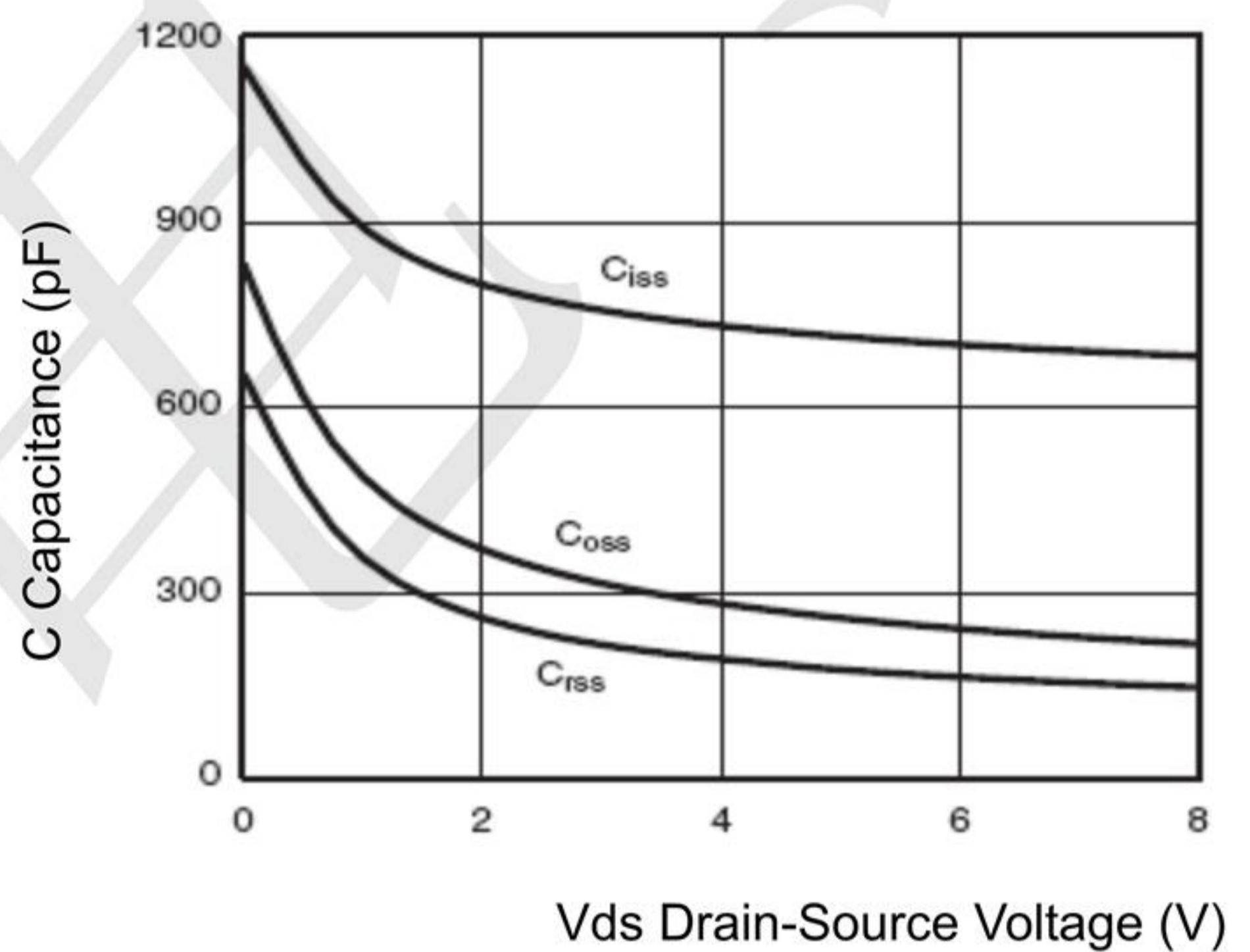
**Figure 7 Transfer Characteristics**



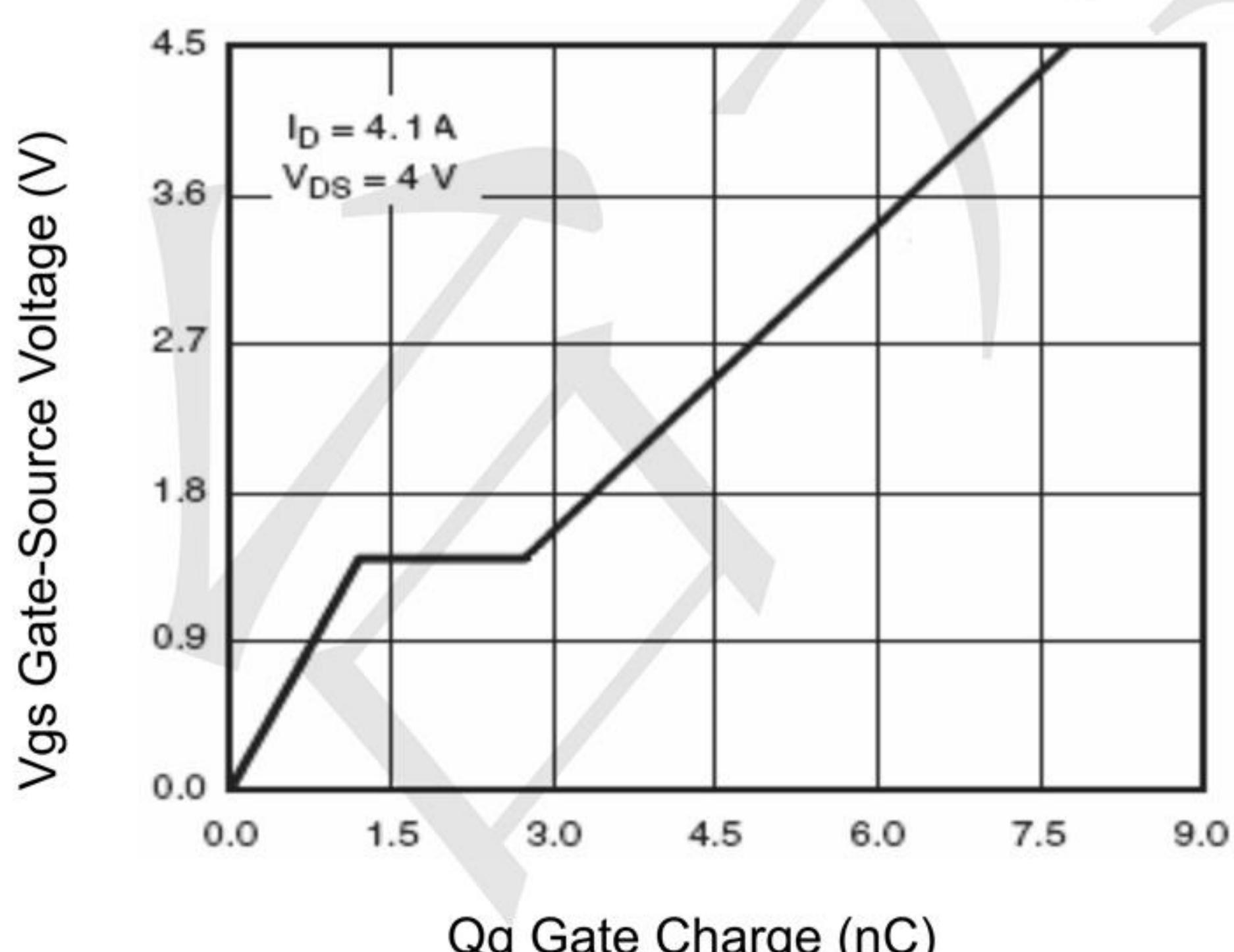
**Figure 8 Drain-Source On-Resistance**



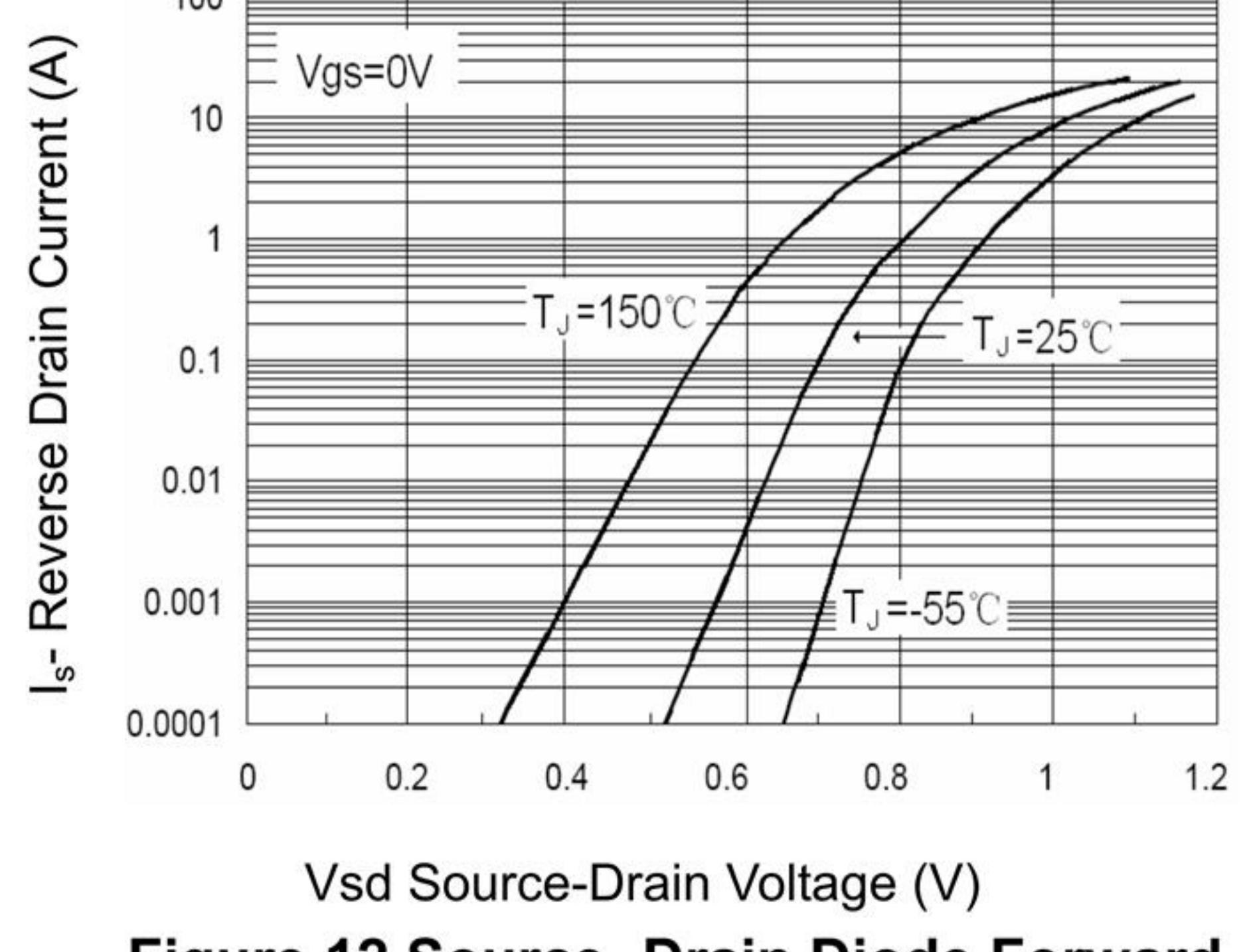
**Figure 9  $R_{DS(on)}$  vs  $V_{GS}$**



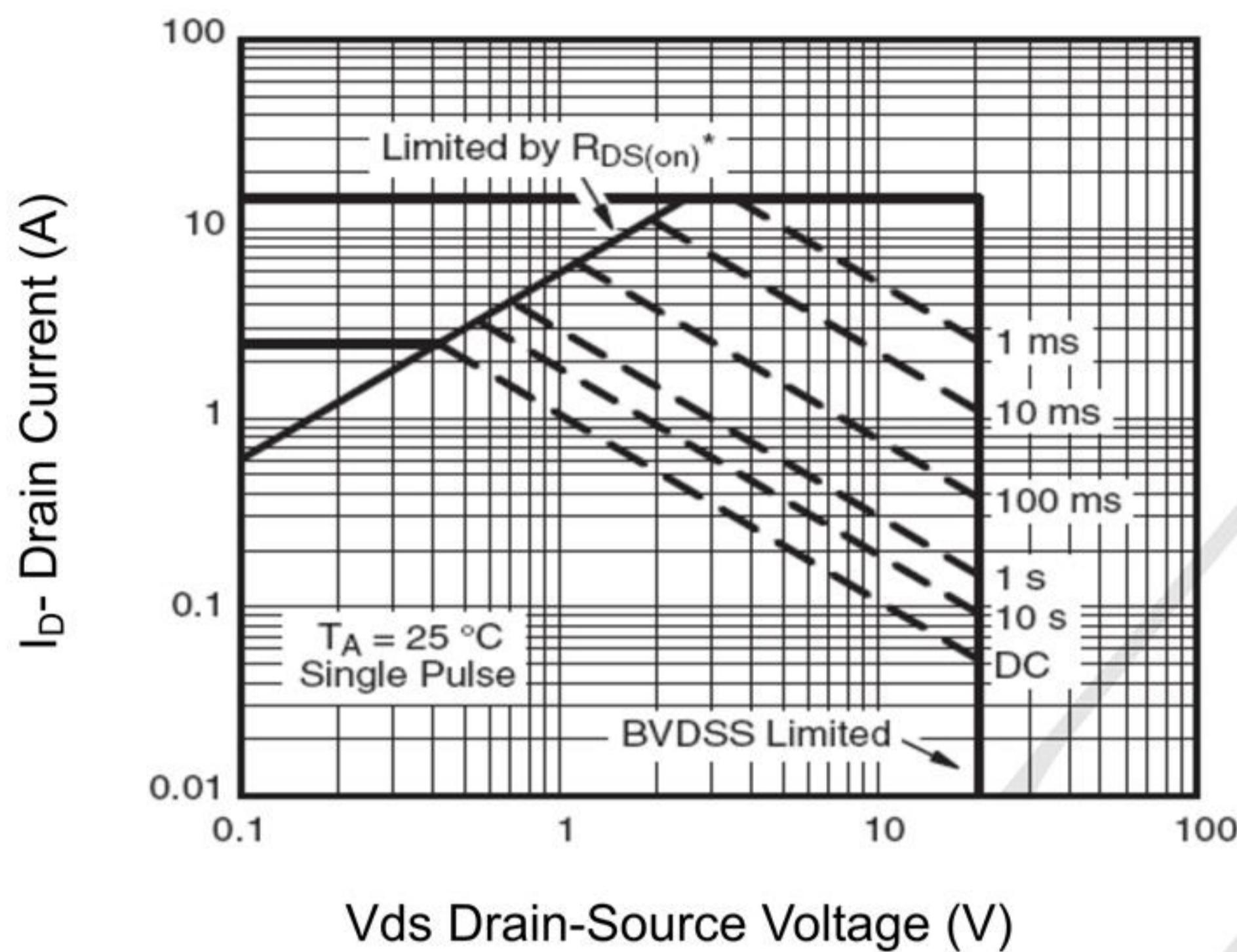
**Figure 10 Capacitance vs  $V_{DS}$**



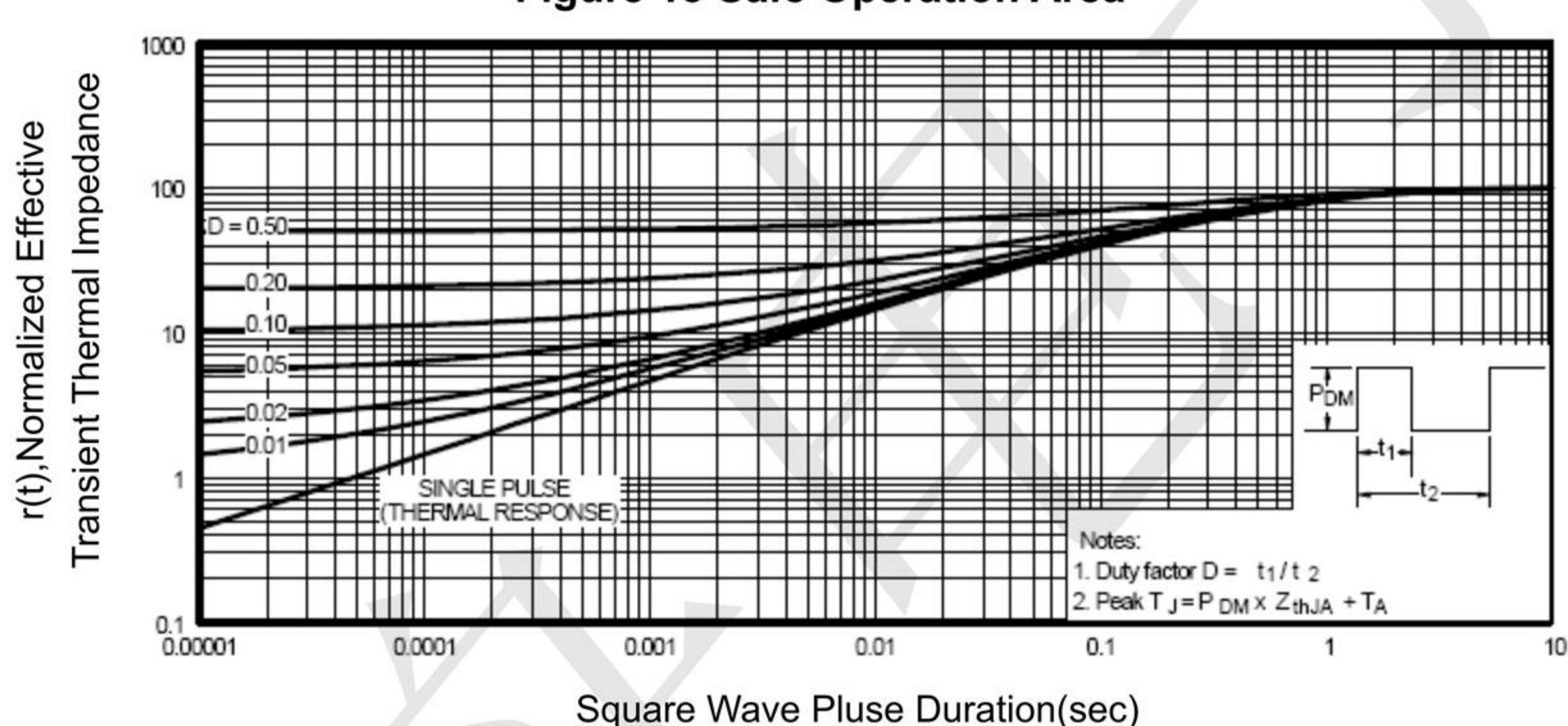
**Figure 11 Gate Charge**



**Figure 12 Source-Drain Diode Forward**



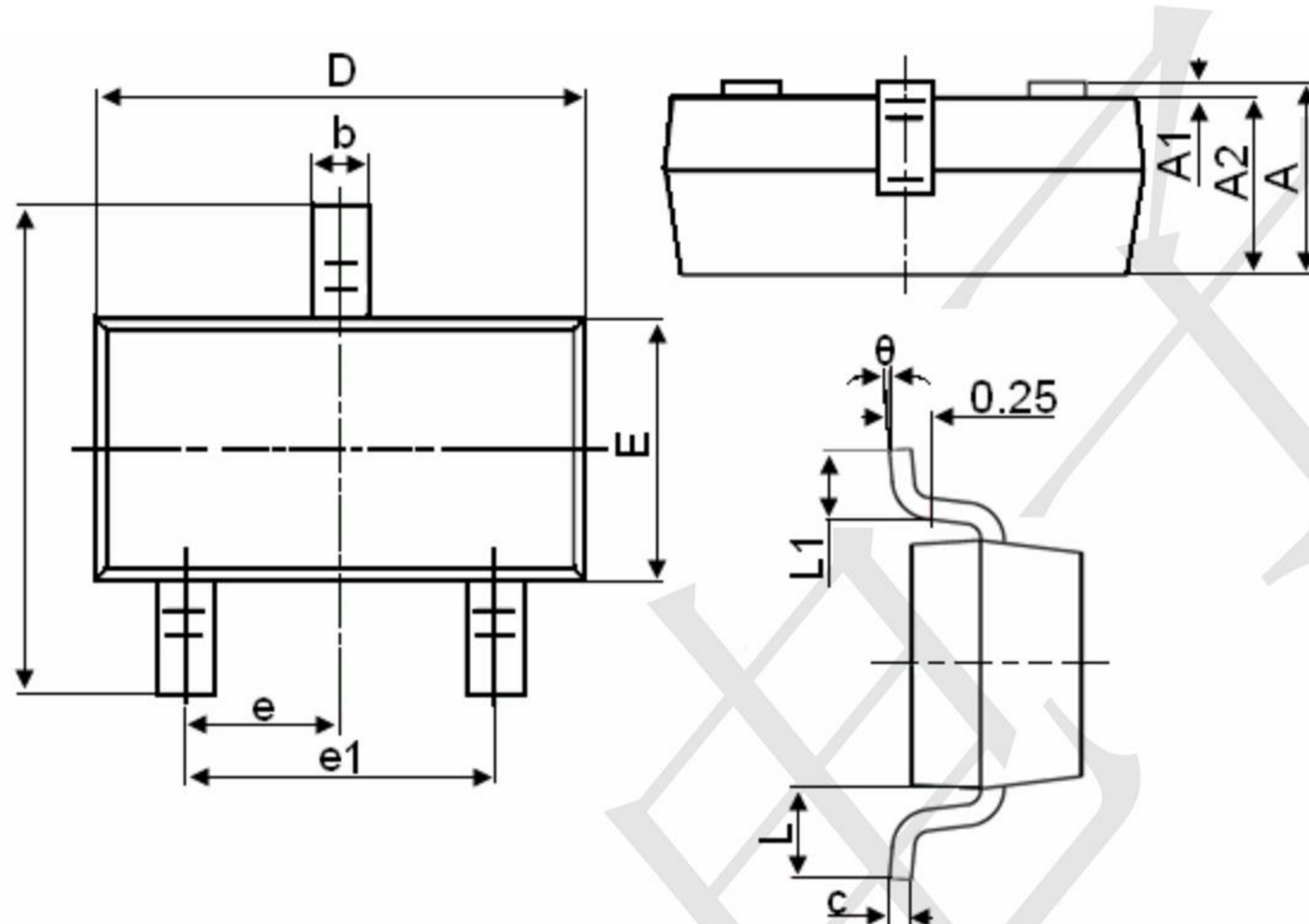
**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**



**SOT-23 Package Information**



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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